

Title: PROCESS FOR FABRICATING A SEMICONDUCTOR DIFFRACTION
GRATING USING A SACRIFICIAL LAYER

Inventor(s): Michael P. Nesnidal et al.
Attorney Docket No. NGC-00087DA (11-0983D)

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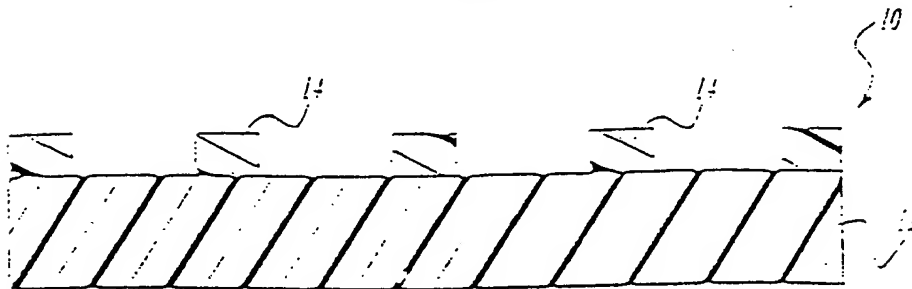


Fig-1

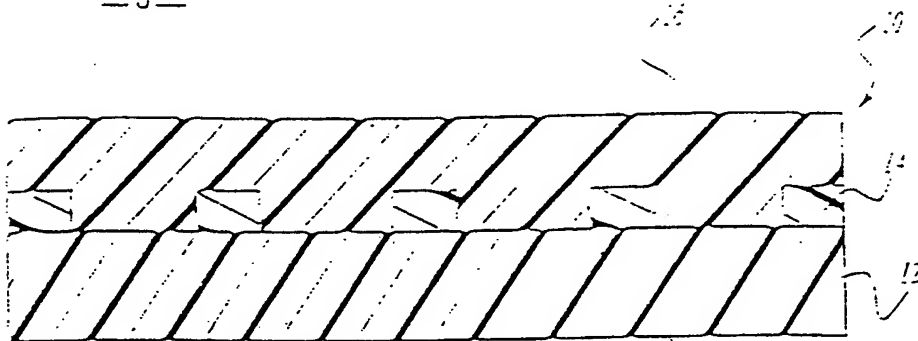


Fig-2

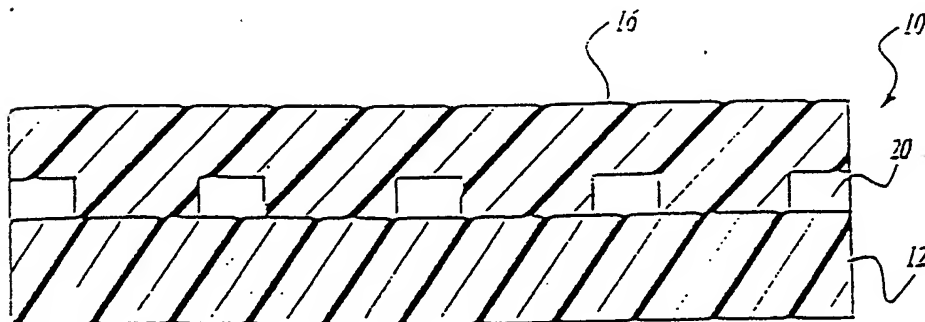


Fig-3

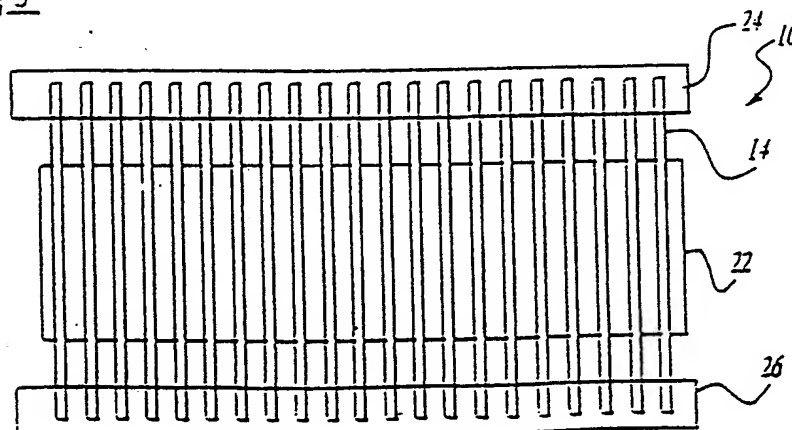


Fig-4

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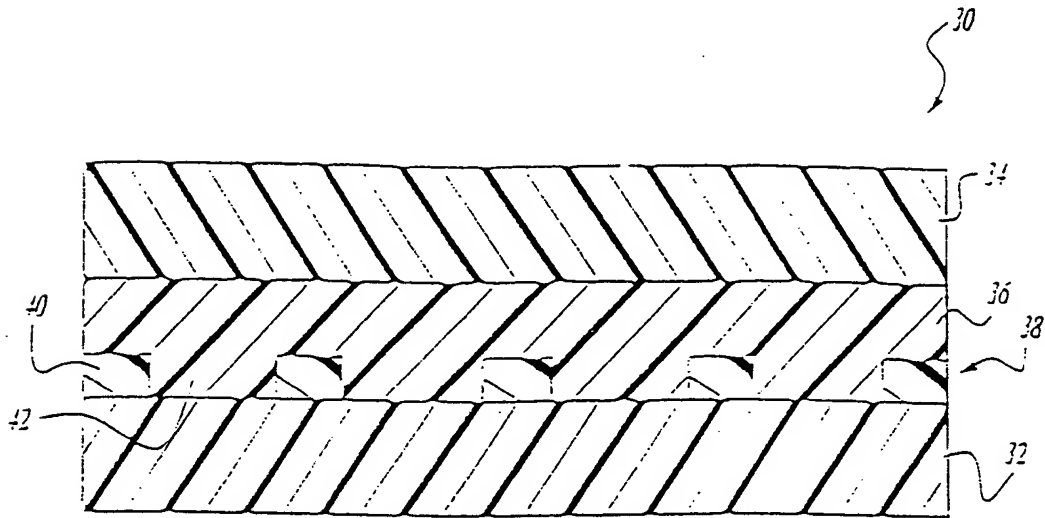


Fig-5

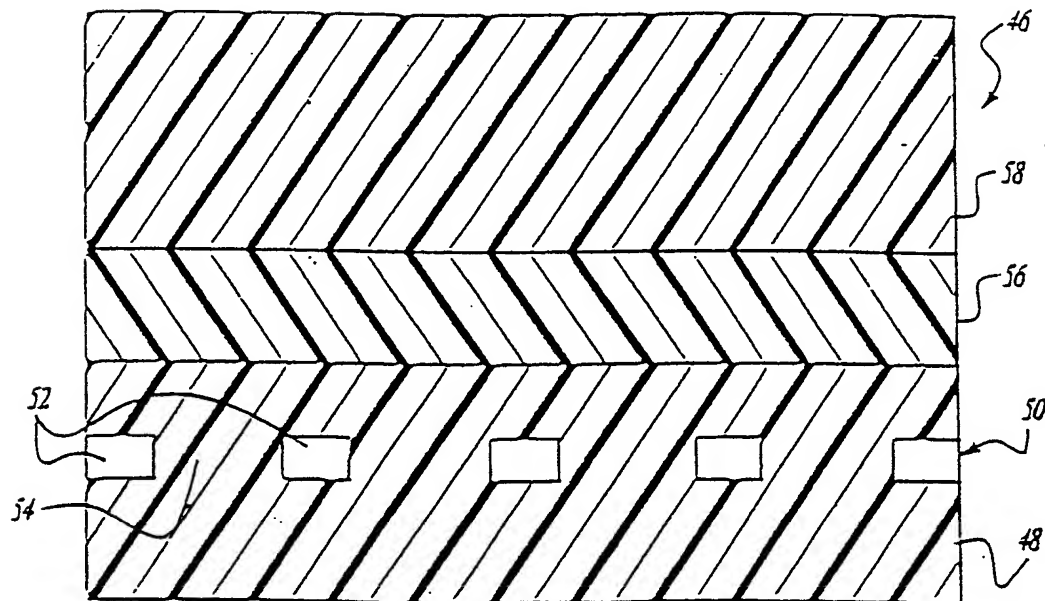


Fig-6

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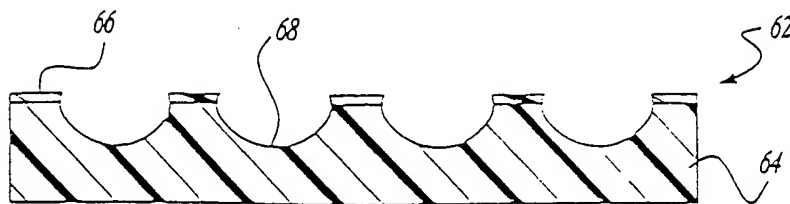


Fig-7

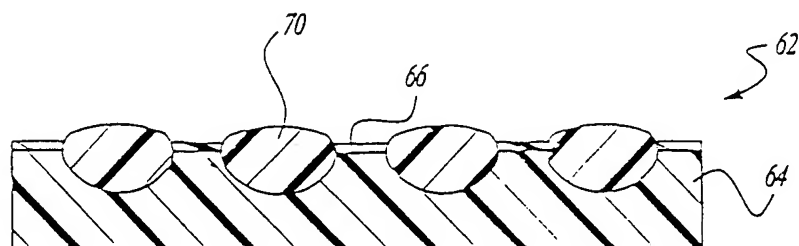


Fig-8

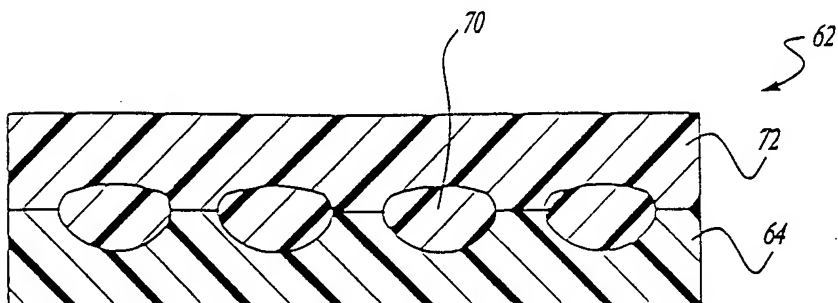


Fig-9

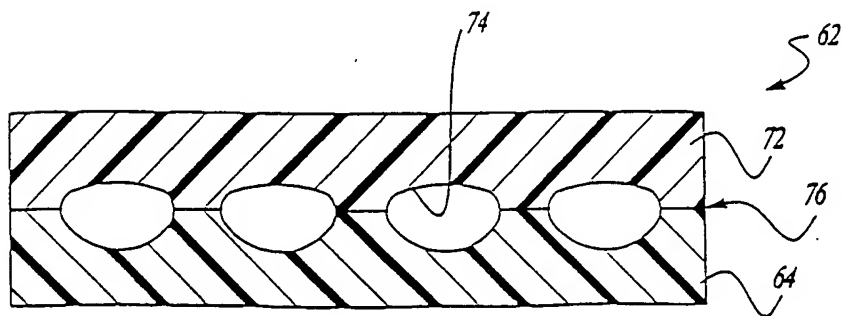


Fig-10